T-33-15

2SC3085



NPN Triple Diffused Planar Silicon Transistor

## Switching Regulator Applications

(E)1055A

## **Features**

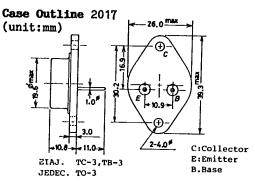
- . Wide ASO.

Absolute Maximum Ratings at Ta	=25 <sup>0</sup> C				unit
Collector to Base Voltage	V <sub>CBO</sub>			500	V
Collector to Emitter Voltage	VCEO			400	V
Emitter to Base Current	V <sub>EBO</sub>			7	V
Collector Current	IC			25	À
Peak Collector Current	icp	PW≤300us, Duty Cycle≤10%		40	A
Base Current	In	* * * =		8	A
Collector Dissipation	Po	Tc=25 <sup>o</sup> C		160	W
Junction Temperature	I <sub>B</sub> P <sub>C</sub> Tj	<del>-</del>		150	°ë
Storage Temperature	Tstg		-55 to		°Č

Electrical Characteristics Collector Cutoff Current		V -1100V T0	min	typ		unit
Emitter Cutoff Current	ICBO IEBO	V <sub>CB</sub> =400V,I <sub>E</sub> =0 V <sub>EB</sub> =5V,I <sub>C</sub> =0			10 10	uA uA
DC Current Gain	h <sub>FE</sub> (1)	$V_{CE}=5V,I_{C}=3.2A$	15#		501	
Gain Bandwidth Product	h <sub>FE</sub> (2)	V <sub>CE</sub> =5V,I <sub>C</sub> =16A	8			• • • •
	$\mathbf{f}_{\mathbf{T}}$	$V_{CE}=10V, \tilde{I}_{C}=3.2A$		20		MHz
Output Capacitance	c <sub>ob</sub>	$V_{CR}=10V, f=1MHz$		320		рF
C-E Saturation Voltage	VCE(sat)	$I_{C}=16A, I_{B}=3.2A$			1.0	v
B-E Saturation Voltage	VBE(sat)	$I_{C}=16A, I_{B}=3.2A$			1.5	V
C-B Breakdown Voltage	V(BR)CBO		500		_	V
C-E Breakdown Voltage	V(BR)CEO	$I_{C}=10$ mA, $\bar{R}_{BE}=\infty$	400			V
E-B Breakdown Voltage	V(BR)EBO		7			v
C-E Sustain Voltage	V <sub>CEO(sus)</sub>	I <sub>C</sub> =25A, L=50uH, I <sub>B</sub> =5A	400			V
C-E Sustain Voltage	VCEX(sus)	I <sub>C</sub> =25A, I <sub>B1</sub> =5A, L=200uH,	400			V
	(1)	I <sub>B2</sub> =-5A, clamped				
C-E Sustain Voltage	V <sub>CEX</sub> (sus)	I <sub>C</sub> =6A, I <sub>B1</sub> =1.2A, L=200uH,	450			V
	(2)	I <sub>B2</sub> =-1.2A, clamped				

\*: The  $h_{FE(1)}$  of the 2SC3085 is classified by 3.2A  $h_{FE}$  as follows. fying the  $h_{FE(1)}$  rank, specify two ranks or more in principle. When speci-

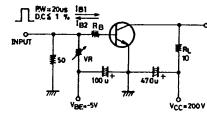
	,					
15 L 30	20	M	40	30	N	50

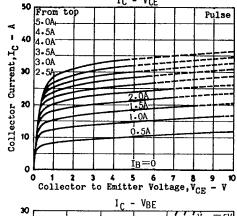


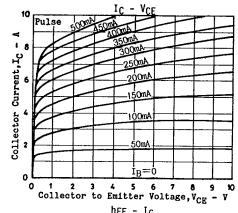
4207KI/2125MW,TS No.1055-1/3

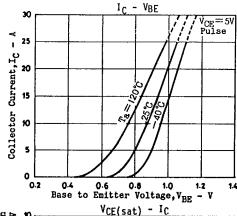
Turn-ON Time	ton	I <sub>C</sub> =20A, I <sub>B1</sub> =4A, I <sub>B2</sub> =-4A, R <sub>L</sub> =10ohm, V <sub>CC</sub> =200V	min	typ	max 1.0	unit us
Storage Time	$^{ extsf{t}}_{ extsf{stg}}$	WF (001m² a CC - 500 a			2.5	us
Fall Time	${f t_f}$	н н			1.0	us

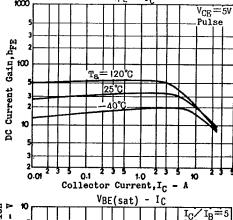
## Switching Time Test Circuit

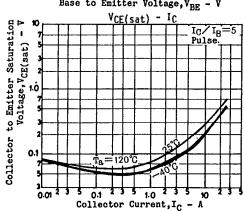


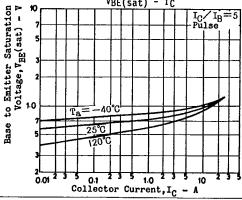






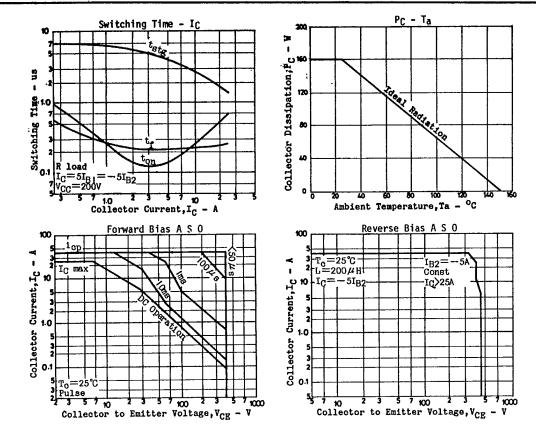






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## CASE OUTLINES AND ATTACHMENTS

- •All of Sanyo Transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- ●No marking is indicated.

